



**THE DATASHEET OF
NRVTSM245ET3G**



NRVTSM245E

Surface Mount Trench Schottky Power Rectifier

POWERMITE® Power Surface Mount Package



ON Semiconductor®

www.onsemi.com

Features

- Low Profile – Maximum Height of 1.1 mm
- Small Footprint – Footprint Area of 8.45 mm²
- Supplied in 12 mm Tape and Reel
- Low Thermal Resistance with Direct Thermal Path of Die on Exposed Cathode Heat Sink
- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- High Surge Capability
- NRV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free and Halide-Free Devices

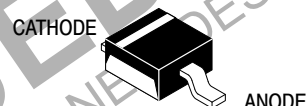
Typical Applications

- Switching Power Supplies including Adapters & Flat Panel Displays
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

Mechanical Characteristics:

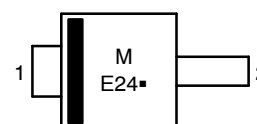
- Powermite is JEDEC Registered as D0-216AA
- Case: Molded Epoxy
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 16.3 mg (Approximately)
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Maximum for 10 Seconds

SCHOTTKY TRENCH RECTIFIER 2.0 AMPERES, 45 VOLTS



POWERMITE
CASE 457

MARKING DIAGRAM



M = Date Code
E24 = Device Code
■ = Pb-Free Package (Marking Style 1)

ORDERING INFORMATION

Device	Package	Shipping†
NRVTSM245ET1G	Powermite (Pb-Free)	3000 / Tape & Reel
NRVTSM245ET3G	Powermite (Pb-Free)	12000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NRVTSM245E

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	45	V
Average Rectified Forward Current ($T_L = 168^\circ\text{C}$)	I_O	2.0	A
Peak Repetitive Forward Current (Square Wave, 20 kHz, $T_L = 167^\circ\text{C}$)	I_{FRM}	4.0	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I_{FSM}	50	A
Storage and Operating Junction Temperature Range (Note 1)	T_{stg}, T_J	-65 to +175	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Lead (Note 2)	Ψ_{JCL}	6.3	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	82	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient (Note 3)	$R_{\theta JA}$	200	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 4) ($I_F = 2\text{ A}$, $T_J = 25^\circ\text{C}$) ($I_F = 2\text{ A}$, $T_J = 125^\circ\text{C}$)	V_F	0.65 0.58	V
Maximum Instantaneous Reverse Current (Note 4) (Rated dc Voltage, $T_J = 25^\circ\text{C}$) (Rated dc Voltage, $T_J = 125^\circ\text{C}$)	I_R	75 3	μA mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Mounted with 700 mm² copper pad size (Approximately 1 in²) 1 oz FR4 Board.
- Mounted with pad size approximately 20 mm² copper, 1 oz FR4 Board.
- Pulse Test: Pulse Width $\leq 380\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

TYPICAL CHARACTERISTICS

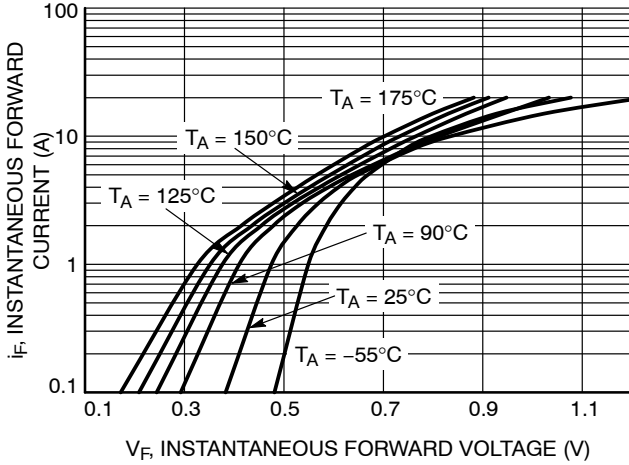


Figure 1. Typical Instantaneous Forward Characteristics

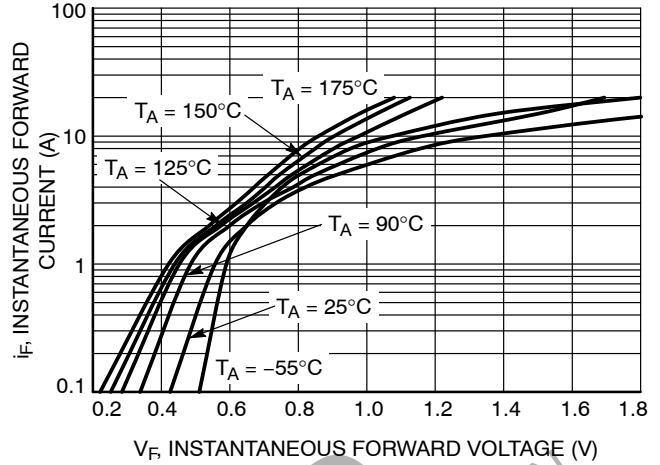


Figure 2. Maximum Instantaneous Forward Characteristics

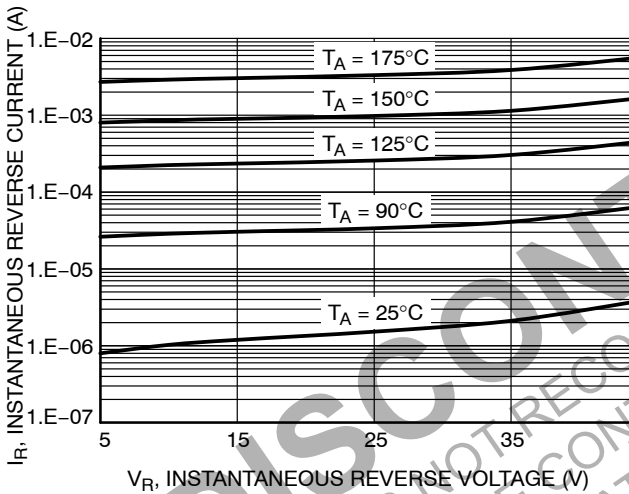


Figure 3. Typical Reverse Characteristics

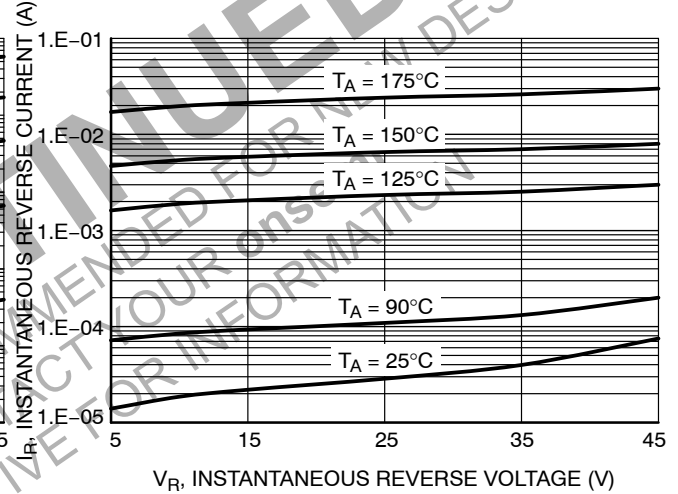


Figure 4. Maximum Reverse Characteristics

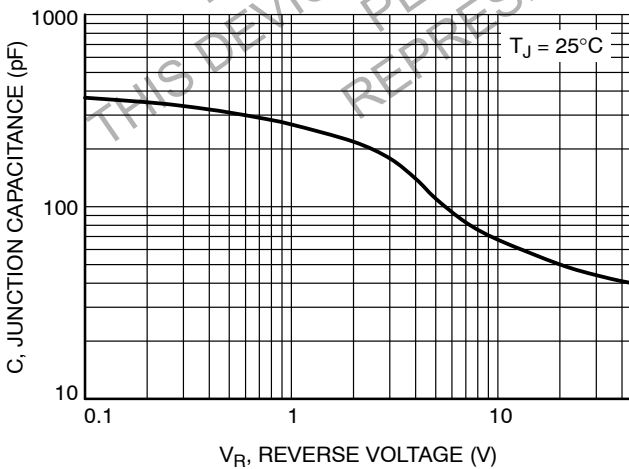


Figure 5. Typical Junction Capacitance

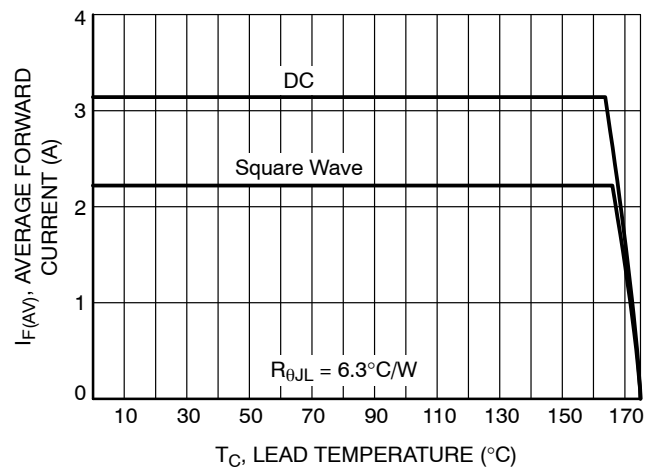


Figure 6. Current Derating

TYPICAL CHARACTERISTICS

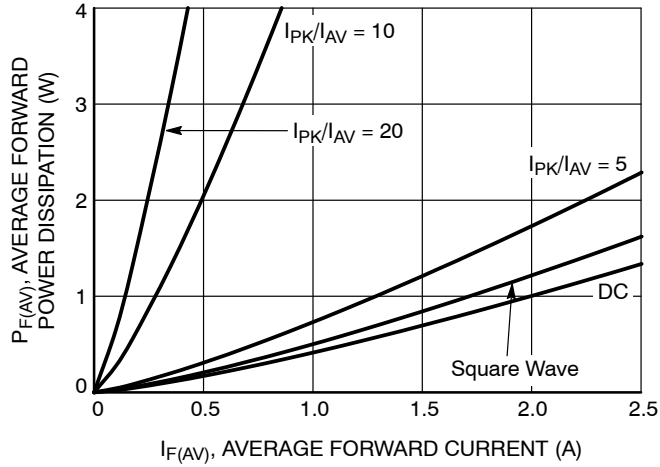


Figure 7. Forward Power Dissipation

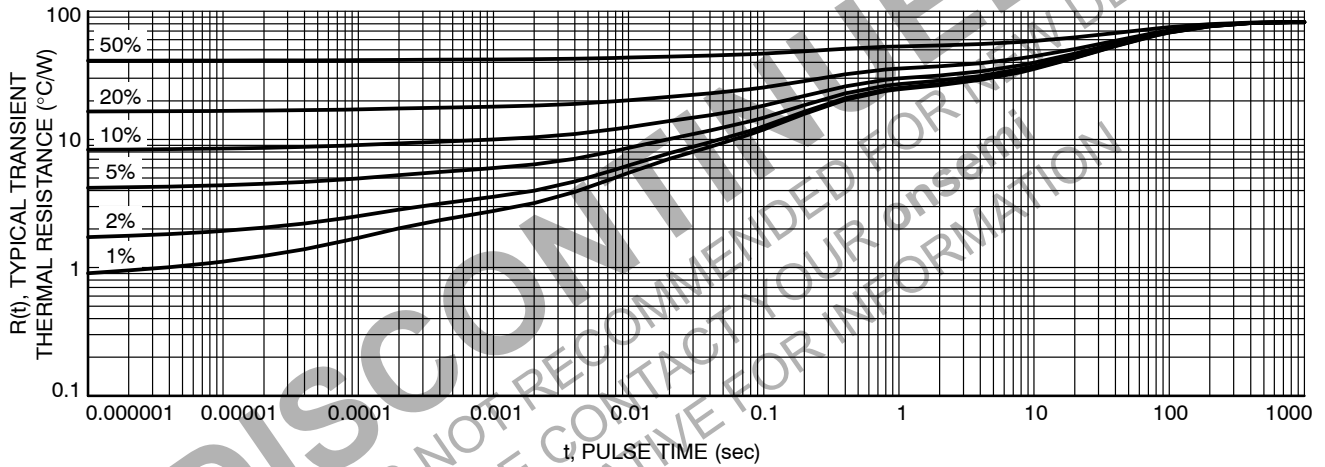
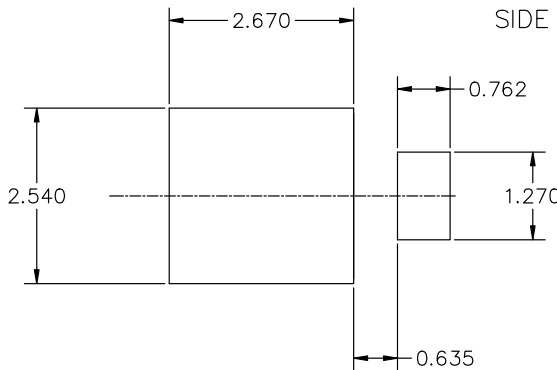
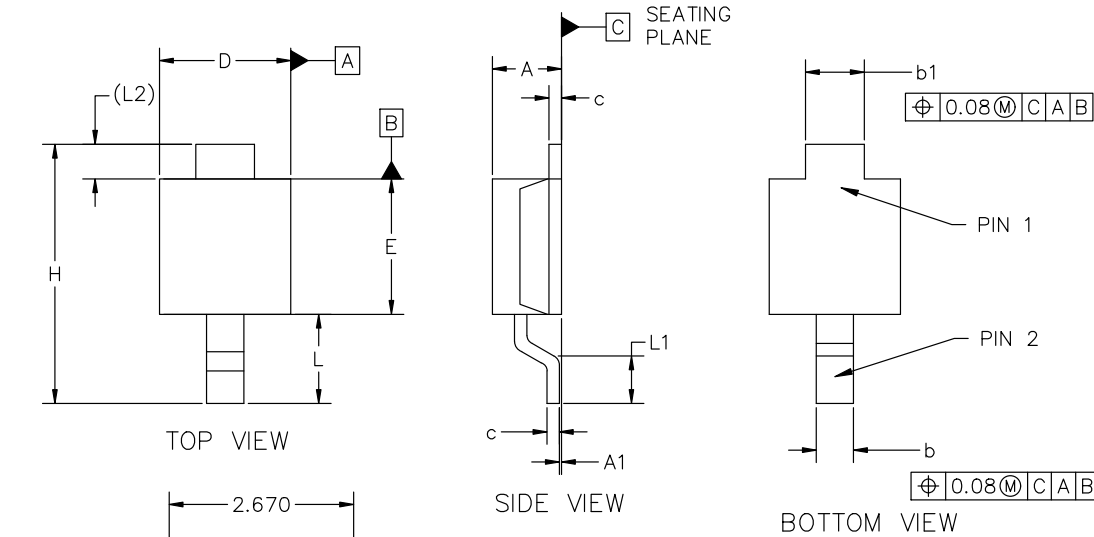


Figure 8. Thermal Response, Junction-to-Ambient



POWERMITE 1.90x1.96x1.00
CASE 457
ISSUE H

DATE 16 MAY 2025



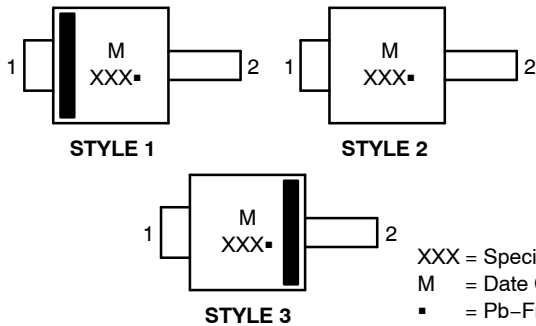
RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free Strategy and Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.85	1.00	1.15
A1	0.00	0.05	0.10
b	0.40	0.55	0.69
b1	0.70	0.85	1.00
c	0.10	0.18	0.25
D	1.75	1.90	2.05
E	1.75	1.96	2.18
H	3.60	3.75	3.90
L	1.20	1.35	1.50
L1	0.50	0.65	0.80
L2	0.50 REF		

- NOTES:
- DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M, 2018.
 - CONTROLLING DIMENSION: MILLIMETERS.
 - DIMENSION D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

GENERIC MARKING DIAGRAMS*



STYLE 1:
PIN 1. CATHODE
2. ANODE

STYLE 2:
PIN 1. ANODE OR CATHODE
2. CATHODE OR ANODE (BI-DIRECTIONAL)

STYLE 3:
PIN 1. ANODE
2. CATHODE

XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	POWERMITE 1.90x1.96x1.00	PAGE 1 OF 1

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